

XG0048(XG3008)

N-Channel Enhancement Mode SGT MOSFET

40V(VDS) / ± 20 V(VGS) / 198A(ID)

Rev0.5

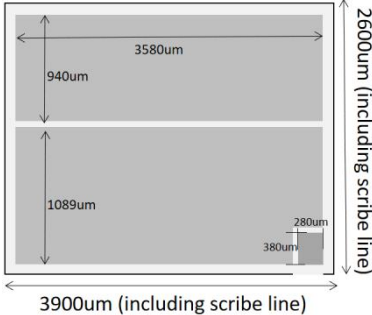


Wafer Specification

1. Order Information

Part No.	Description	Gross die / per 8" wafer
XG0048(XG3008)	40V(V_{DS}) / $\pm 20V(V_{GS})$/ 198A(I_D) N-Channel Enhancement Mode SGT MOSFET	2,769

2. Physical Characteristics

	Die Size: 3900 μ m $\times$ 2600 μ m (including scribe line)
	Gate: 280 μ m $\times$ 380 μ m
	For PDFN5X6 package Suggest Bonding wire: Gate: 1.7mil PdCu Source: 80*4mil Ribbon

3. Mechanical Data

Nominal Back Metal Composition, Thickness	Ti-Ni-Ag (13kA°)
Nominal Front Metal Composition, Thickness	AlCu (5.5 μ m)
Wafer Diameter	200mm, with 010 notch
Wafer Thickness	125 μ m $\pm$ 10 μ m
Scribe Line Width	80 μ m

4. Key Electrical Characteristics of Die (at $T_J = 25^\circ\text{C}$, unless otherwise specified)S

Parameter	Description	Min.	Typ.	Max.	Unit	Test Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	40			V	V _{GS} =0V, I _D =250μA
I _{D(Device Ref)}	Continuous Drain Current			198	A	T _J =25°C
R _{DS(on)} (FT)	Static Drain-to-Source On-Resistance		1.15	1.6	mΩ	V _{GS} =10V, I _D =15A
V _{GS(th)}	Gate Threshold Voltage		2.8	3.4	V	V _{DS} =V _{GS} , I _D =250μA
I _{DSS}	Drain-to-Source Leakage Current			1.0	μA	V _{DS} =40V, V _{GS} =0V
I _{GSS}	Gate-to-Source Leakage Current			±100	nA	V _{GS} =±20V, V _{DS} =0V
E _{AS}	Single Pulsed Avalanche Energy			900	mJ	L=0.5mH, V _{DD} =20V
R _g	Gate Poly Resistance		1.1		Ω	V _{DS} =0V, V _{GS} =0, f=1MHZ
C _{iss}	Input Capacitance		5800		pF	V _{DS} =20V, V _{GS} =0, f=1MHZ
C _{oss}	Output Capacitance		3200		pF	
C _{rss}	Reverse Transfer Capacitance		240		pF	
T _J , T _{STG}	Operating and Storage Temperature	-55°C to 150°C Max				